

MOSFET - Power, Single N-Channel, TOLL

NTBLS1D5N08MC 80 V, 1.53 mΩ, 298 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Lowers Switching Noise/EMI
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	80	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJC} (Note 2)	Steady State	T _C = 25°C	I _D	298	A
Power Dissipation R _{θJC} (Note 2)		T _C = 25°C	P _D	250	W
Continuous Drain Current R _{θJA} (Notes 1, 2)	Steady State	T _A = 25°C	I _D	32	A
Power Dissipation R _{θJA} (Notes 1, 2)		T _A = 25°C	P _D	2.9	W
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		I _{DM}	4487	A
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +150	°C
Source Current (Body Diode)			I _S	192	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 31 A, L = 3 mH)			E _{AS}	1441	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	0.5	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	43	

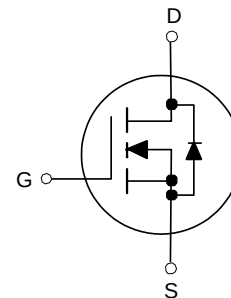
1. Surface-mounted on FR4 board using a 1 in² pad size, 1 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.



ON Semiconductor®

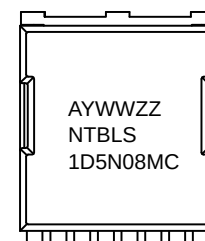
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	1.53 mΩ @ 10 V	298 A
	3.7 mΩ @ 6 V	



MO-299A
TOLL
CASE 100CU

MARKING DIAGRAM



NTBLS1D5N08MC = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NTBLS1D5N08MC

Table 1. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Units	
OFF CHARACTERISTICS								
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$		80	–	–	V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		–	78	–	mV/ $^\circ\text{C}$	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\ \text{V}$, $V_{GS} = 0\ \text{V}$	$T_J = 25^\circ\text{C}$	–	–	1	μA	
			$T_J = 125^\circ\text{C}$	–	–	100	μA	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$		–	–	± 100	nA	
ON CHARACTERISTICS (Note 3)								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_D = 710\ \mu\text{A}$		2.0	3.0	4.0	V	
Negative Threshold Temperature Coefficient	$V_{GS(th)}/T_J$	$I_D = 710\ \mu\text{A}$, ref to 25°C		–	–8.3	–	mV/ $^\circ\text{C}$	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 80\ \text{A}$		–	1.30	1.53	m Ω	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 6\ \text{V}$, $I_D = 63\ \text{A}$		–	2.0	3.7	m Ω	
Forward Transconductance	g_{FS}	$V_{DS} = 5\ \text{V}$, $I_D = 80\ \text{A}$		–	220	–	S	
Gate-Resistance	R_G	$T_A = 25^\circ\text{C}$		–	0.7	–	Ω	
CHARGES & CAPACITANCES								
Input Capacitance	C_{iss}	$V_{GS} = 0\ \text{V}$, $V_{DS} = 40\ \text{V}$, $f = 1\ \text{MHz}$		–	8170	–	pF	
Output Capacitance	C_{oss}			–	3025	–	pF	
Reverse Transfer Capacitance	C_{rss}			–	82	–	pF	
Total Gate Charge	$Q_{G(tot)}$	$V_{GS} = 10\ \text{V}$, $V_{DS} = 40\ \text{V}$, $I_D = 80\ \text{A}$		–	111	–	nC	
Threshold Gate Charge	$Q_{G(th)}$			–	22	–		
Gate-to-Source Charge	Q_{gs}			–	35	–		
Gate-to-Drain Charge	Q_{gd}			–	23	–		
Output Charge	Q_{oss}			–	166	–		
Sync Charge	Q_{sync}			–	94	–		
Plateau Voltage	V_P			–		5	–	V
SWITCHING CHARACTERISTICS, $V_{GS} = 10\ \text{V}$ (Note 3)								
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\ \text{V}$, $V_{DS} = 40\ \text{V}$, $I_D = 80\ \text{A}$, $R_G = 6\ \Omega$		–	38	–	ns	
Rise Time	t_r			–	34	–	ns	
Turn-Off Delay Time	$t_{d(off)}$			–	74	–	ns	
Fall Time	t_f			–	37	–	ns	
DRAIN-SOURCE DIODE CHARACTERISTICS								
Forward Diode Voltage	V_{SD}	$I_S = 80\ \text{A}$, $V_{GS} = 0\ \text{V}$	$T_J = 25^\circ\text{C}$	–	0.8	1.3	V	
		$I_S = 80\ \text{A}$, $V_{GS} = 0\ \text{V}$	$T_J = 125^\circ\text{C}$	–	0.7	–	V	
Reverse Recovery Time	t_{rr}	$I_F = 40\ \text{A}$, $di/dt = 300\ \text{A}/\mu\text{s}$		–	19	–	nS	
Reverse Recovery Charge	Q_{rr}			–	42	–	nC	
Reverse Recovery Time	t_{rr}	$I_F = 40\ \text{A}$, $di/dt = 1000\ \text{A}/\mu\text{s}$		–	17	–	nS	
Reverse Recovery Charge	Q_{rr}			–	121	–	nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

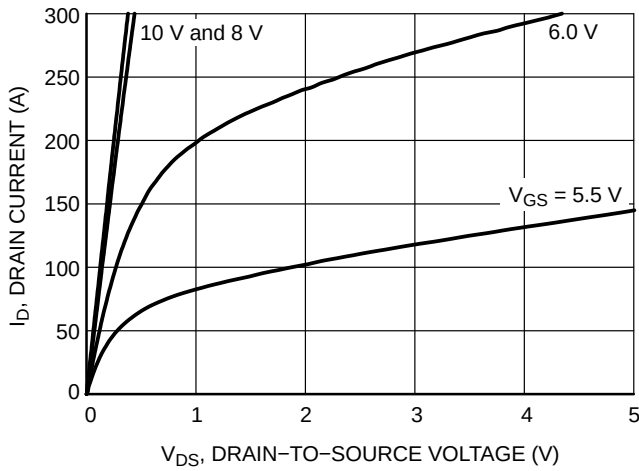


Figure 1. On-Region Characteristics

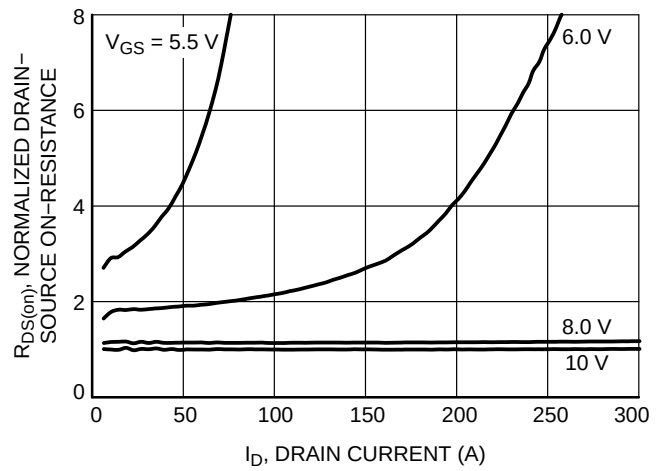


Figure 2. $R_{DS(on)}$ Normalized vs. I_D

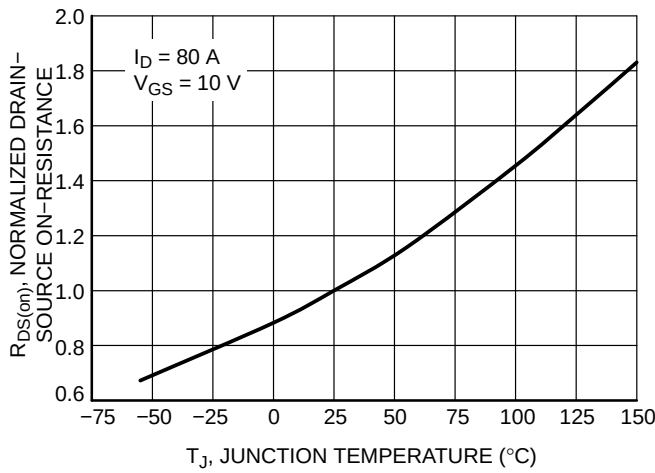


Figure 3. $R_{DS(on)}$ vs. Junction Temperature

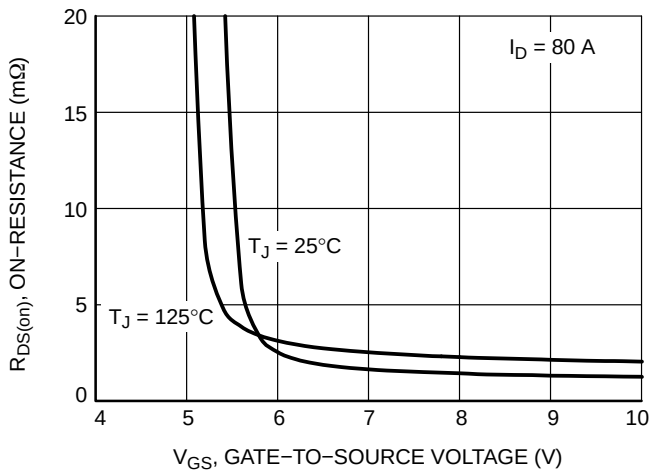


Figure 4. On-Resistance vs. Gate-to-Source Voltage

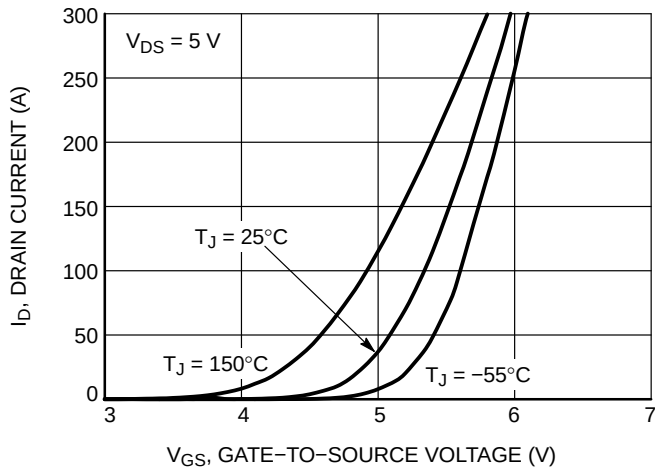


Figure 5. Drain Current vs. Gate-to-Source Voltage

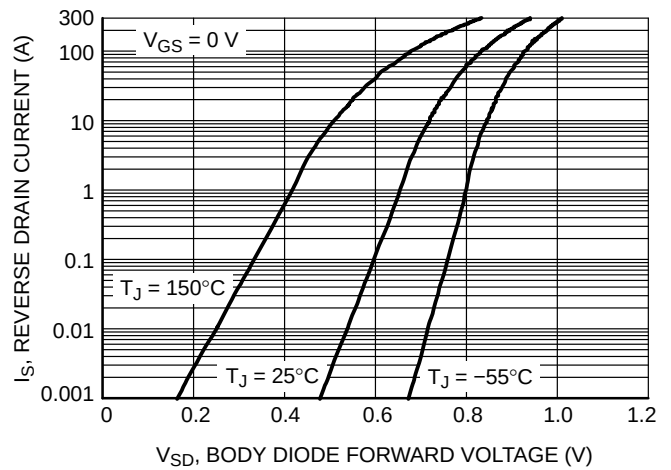


Figure 6. Reverse Drain Current vs. Body Diode Forward Voltage

TYPICAL CHARACTERISTICS

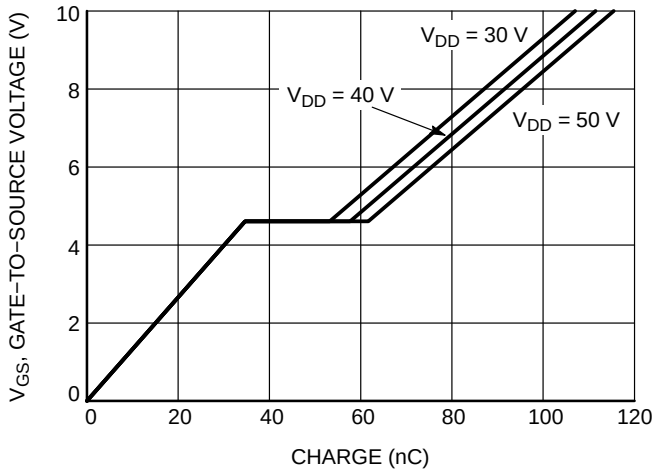


Figure 7. Gate Charge

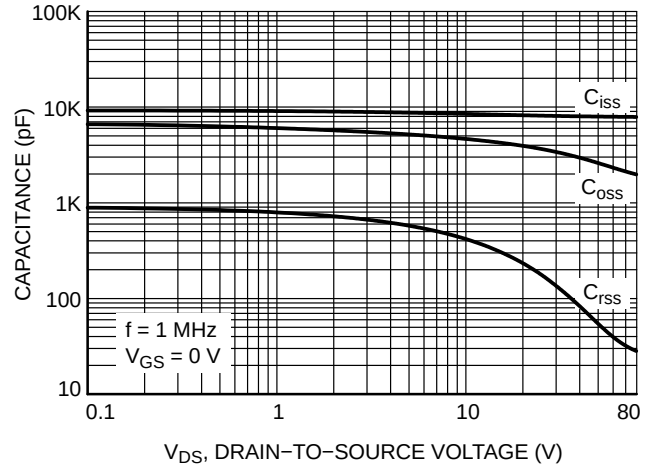


Figure 8. Capacitance Variation

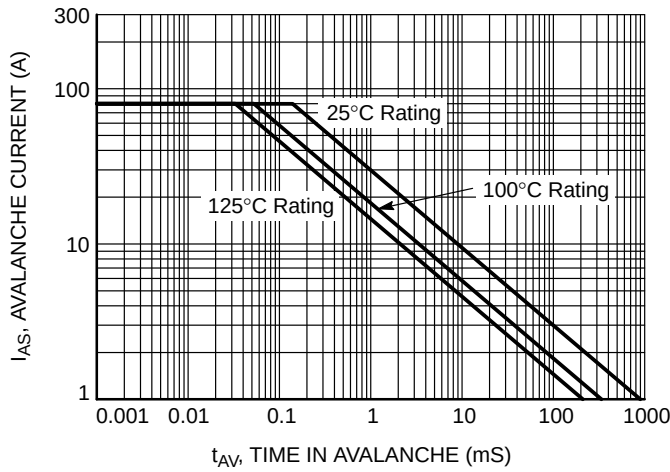


Figure 9. UIL

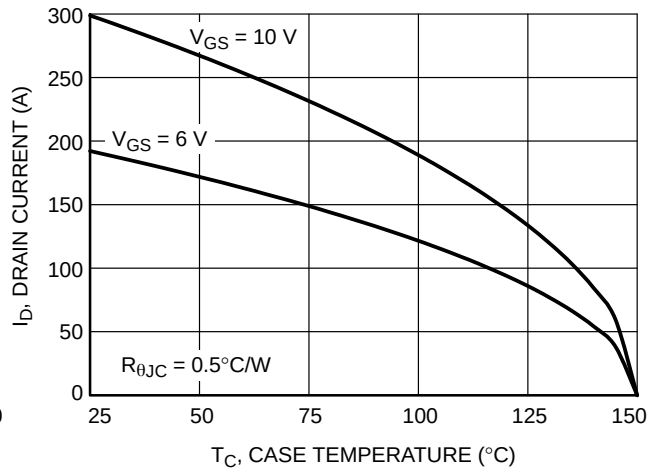


Figure 10. Drain Current vs. Case Temperature

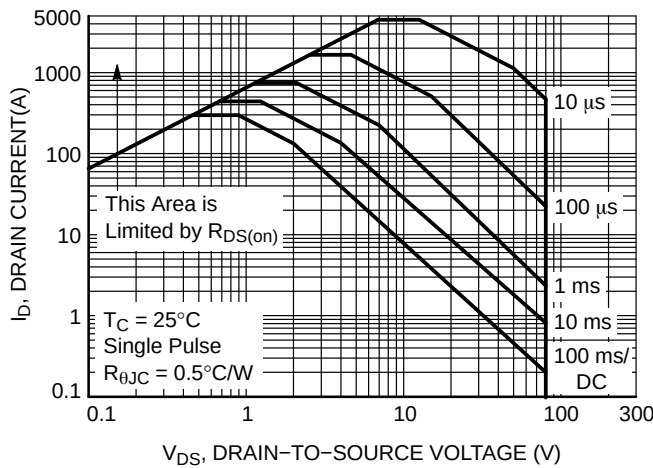


Figure 11. Maximum Rated Forward Biased Safe Operating Area

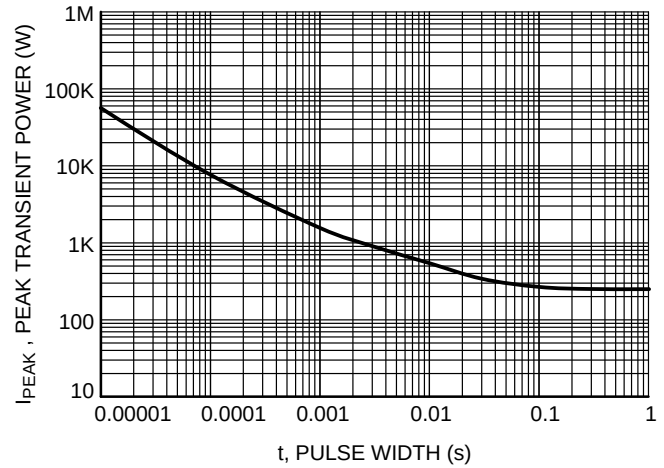


Figure 12. Peak Power

NTBLS1D5N08MC

TYPICAL CHARACTERISTICS

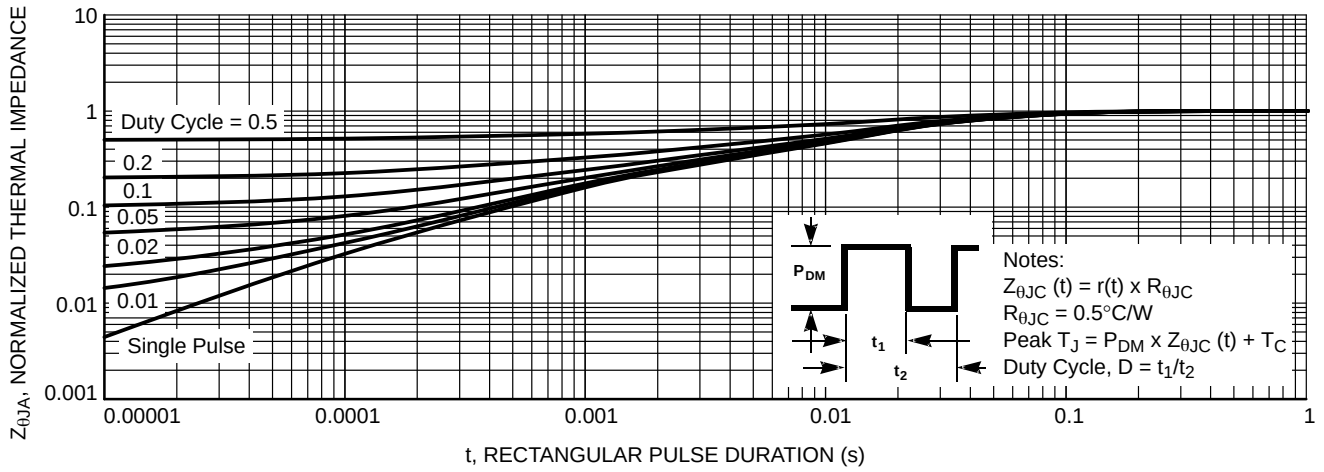


Figure 13. Transient Thermal Impedance

DEVICE ORDERING INFORMATION

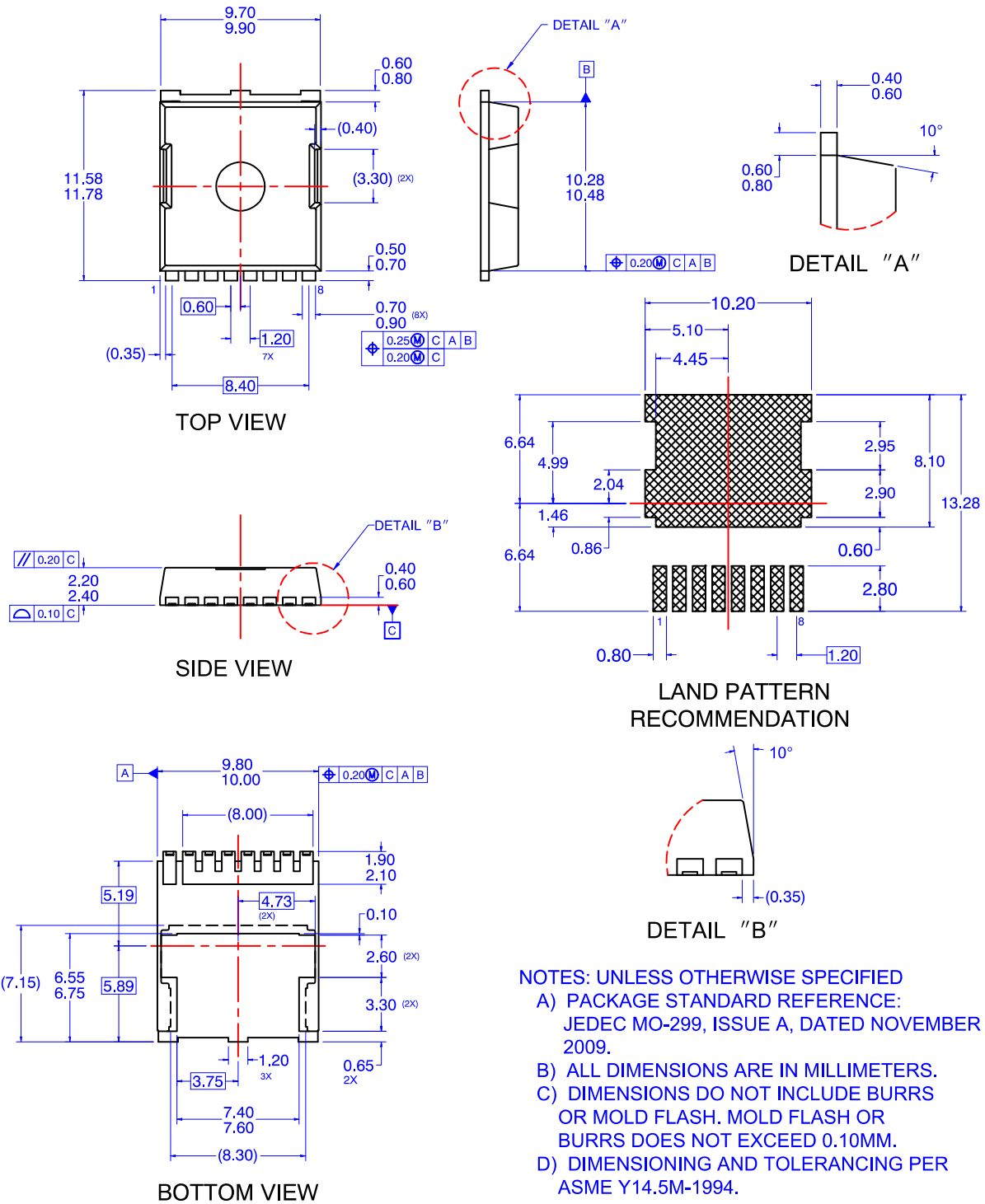
Device	Marking	Package	Shipping [†]
NTBLS1D5N08MC	NTBLS 1D5N08MC	M0-299A (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTBLS1D5N08MC

PACKAGE DIMENSIONS

H-PSOF8L 11.68x9.80
CASE 100CU
ISSUE O



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